

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	electrode near rhodium near iridium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:32
L2	3	electrode near rh near ir	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:30
L3	0	conductor near rhodium near iridium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:33
L4	1	conductor near rh near ir	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:32
L5	9	conductive near rhodium near iridium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:35
L6	3	conductive near rh near ir	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:34
L7	0	conduction near rhodium near iridium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:37
L8	0	conduction near rh near ir	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:35

L10	0	conducting near rhodium near iridium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:37
L11	7	conducting near rh near ir	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:37
L12	268	metal near rhodium near iridium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 08:53
L13	62	metal near rh near ir	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:51
L14	509	two adj layer adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:56
L15	5	(two adj layer adj electrode) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:57
L16	2	(two adj layer adj electrode) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 09:53
L18	55	(electrode adj stack) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:22

L19	16	(multilayer adj electrode) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:26
L20	61	(electrode adj stack) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:06
L21	14	(multilayer adj electrode) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:20
L22	0	(conductor adj stack) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:25
L23	0	(conductive adj stack) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:24
L24	0	(conducting adj stack) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:24
L25	0	(conduction adj stack) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:24
L26	5	(conductor adj stack) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:23

L27	0	(conductive adj stack) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:24
L28	0	(conducting adj stack) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:24
L29	0	(conduction adj stack) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:24
L30	8	(metal adj stack) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:26
L31	2	(metal adj stack) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:25
L32	0	(metallic adj stack) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:26
L33	0	(metallic adj stack) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:26
L34	5	(multilayer adj metal) and (rhodium near iridium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:27

L35	14	(multilayer adj metal) and (rh near ir)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:29
L36	0	iridium adj (layer or film) adj (disposed or formed or deposited) adj rhodium adj (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:30
L37	0	ir adj (layer or film) adj (disposed or formed or deposited) adj rh adj (layer or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:30
L38	0	(iridium adj (layer or film)) near (disposed or formed or deposited) near (rhodium adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:31
L39	10	(iridium adj (layer or film)) with (disposed or formed or deposited) with (rhodium adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:36
L40	8	(ir adj (layer or film)) with (disposed or formed or deposited) with (rh adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:30
L41	10	sonobe-shinya.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:37
L42	2	sonobe-shinya.inv. and (ir or iridium) and (rh or rhodium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 10:37

L43	1997	257/99.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:10
L44	12	257/99.ccls. and (ir or iridium) and (rh or rhodium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:27
L46	953	"257"/\$.ccls. and ((ir or iridium) near (rh or rhodium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:29
L47	0	"257"/\$.ccls. and ((ir or iridium) near (rh or rhodium) near electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:29
L48	2	"257"/\$.ccls. and ((ir or iridium) near (rh or rhodium) near conductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:29
L49	7	(ir adj (layer or film)) with (over or above or atop) with (rh adj (layer or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 11:31